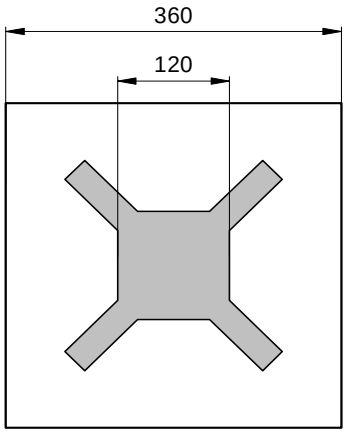
LED - Chip

ELC-950-17

15.02.2012 rev. 05

Radiation	Type	Technology	Electrodes
Infrared	DH	AlGaAs/GaAs	P (anode) up



LED-14

typ. dimensions (µm)

typ. thickness
260 (±20) µm

anode
gold alloy, 1.5 µm

cathode
gold alloy, 0.5 µm,

Maximum Ratings

Tamb = 25℃, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			100	mA

Optical and Electrical Characteristics

T_{amb} = 25℃, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F		1.2	1.4	V
Forward voltage	I_F = 100 mA	V_F		1.35	1.7	V
Reverse voltage	I_R = 100 µA	V_R	5			V
Radiant power*	I_F = 20 mA	Φ_e	1.2	2.5		mW
Radiant power*	I_F = 100 mA	Φ_e		10.5		mW
Centroid wavelength	I_F = 20 mA	λ_p	935	950	960	nm
Spectral bandwidth at 50%	I_F = 20 mA	$\Delta\lambda_{0.5}$		50		nm
Switching time	I_F = 20 mA	t_r, t_f		450/300		ns

*Measured on bare chip on TO-18 header with JENOPTIK Polymer Systems equipment

Labeling

Type	Lot N°	Φ_e(typ) [mW]	V_F(typ) [V]	Quantity
ELC-950-17				

Packing: Chips on adhesive film with wire-bond side on top

JENOPTIK Polymer Systems GmbH, D-12555 Berlin, Köpenicker Str.325 b, Haus 201
Tel.: +49-30-6576 2543, Fax : +49-30-6576 2545